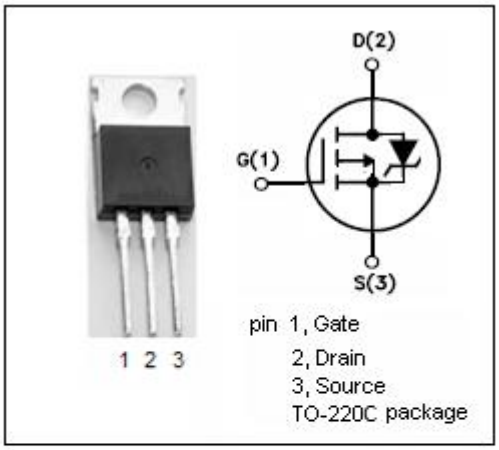
isc P-Channel MOSFET Transistor IRFP9530

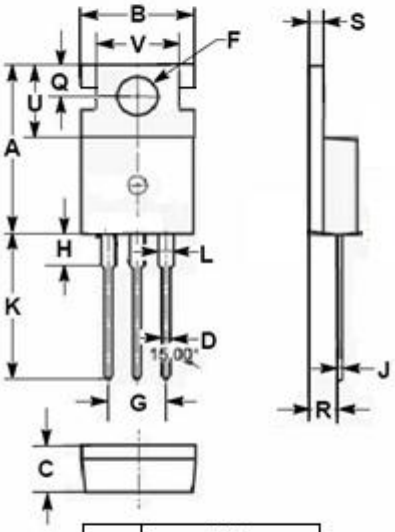


FEATURES

- Drain Current I_D= -12A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= -100V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 0.3Ω(Max)
- Fast Switching

DESCRIPTION

- Designed for use in switch mode power supplies and general purpose applications.



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	-12	A
I_{DM}	Drain Current-Single Pluse	-48	A
P_D	Total Dissipation @T_C=25℃	76	W
T_J	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	0.7	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	30	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= -0.25mA	-100		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=- 0.25mA	-2	-4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D= -6.5A		0.3	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0		±500	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -100V; V_{GS}= 0		-250	μA
V_{SD}	Forward On-Voltage	I_S= -12A; V_{GS}= 0		-6.3	V